HFZT

KTB1366

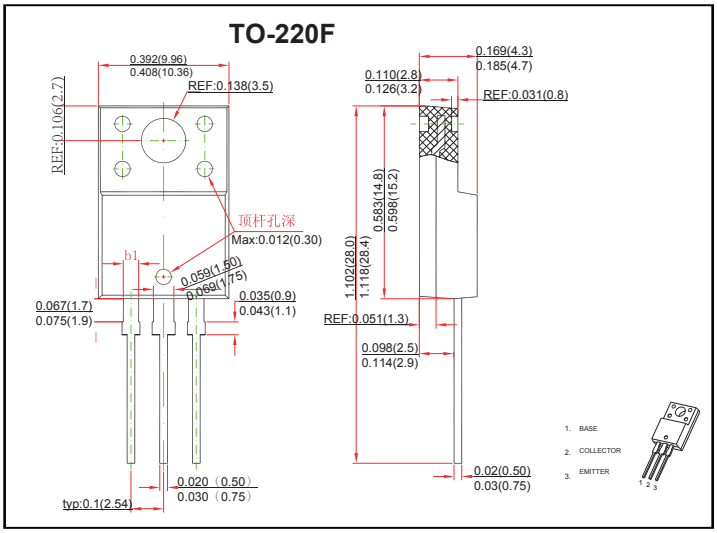
TO-220F Plastic-Encapsulate Transistors

FEATURES

- Low $V_{CE(sat)}$: $V_{CE(sat)}$=-1.0V(Max.)(I_C/I_B=-2A/-0.2A)
- Complementary to KTD2058
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style:TO-220F molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector power dissipation	2	W
T_J	Junction temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-1mA, I_E=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-50mA, I_B=0	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-1mA, I_C=0	-7			V
Collector cut-off current	I_{CBO}	V_{CB}=-60V, I_E=0			-100	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-7V, I_C=0			-100	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-5V, I_C=-0.5A	60		200	
	$h_{FE(2)}$	V_{CE}=-5V, I_C=-3A	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-2A, I_B=-0.2A			-1	V
Base-emitter voltage	V_{BE}	V_{CE}=-5V, I_C=-0.5A			-1	V
Transition frequency	f_T	V_{CE}=-5V, I_C=-0.5A		9		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		150		pF
Fall time	t_f	I_C=-2A, I_{B1}=-I_{B2}=-0.2A, V_{CC}=-30V		0.4		μs
Storage time	t_s			1.7		μs

CLASSIFICATION of $h_{FE(1)}$

Rank	O	Y
Range	60-120	100-200